SCAS347E - MARCH 1994 - REVISED JUNE 1998

- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

(TOP VIEW) 24 🛮 V_{CC} OE1 A1 [2 23 Y1 A2 🛮 3 22 Y2 A3 🛮 4 21 Y3 A4 🛮 5 20 Y4 A5 🛮 6 19 Y5 18**∏** Y6 A6 ∏ 7 A7 **∏**8 17**∏** Y7 16 Y8 A8 [] 9 A9 🛮 10 15 Y9

A10 ∏ 11

12

GND [

14 Y10

13 OE2

DB, DW, OR PW PACKAGE

description

This 10-bit buffer/bus driver is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74LVC828A provides a high-performance bus interface for wide data paths or buses carrying parity.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all ten outputs are in the high-impedance state. The SN74LVC828A provides inverting data at its outputs.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC828A is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

	INPUTS	OUTPUT	
OE1	OE2	Α	Y
L	L	L	Н
L	L	Н	L
Н	X	Χ	Z
Х	Н	Χ	Z



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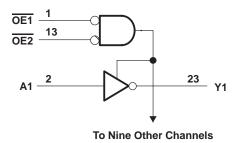
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logic symbol†

OE1 ΕN 13 OE2 23 **Y**1 **A1** 3 22 **Y2 A2** 4 21 **Y3** A3 5 20 Α4 Υ4 6 19 Α5 **Y5** 7 18 **Y6** Α6 8 17 **Y7 A7** 16 Y8 **A8** 10 15 Α9 Y10 A10

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V _{CC}	–0.5 V to 6.5 V
Input voltage range, V _I (see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, VO	
(see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DB package	104°C/W
DW package	81°C/W
PW package	120°C/W
Storage temperature range, T _{stq}	–65°C to 150°C

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The value of V_{CC} is provided in the recommended operating conditions table.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.



[†]This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
\/	Supply voltage	Operating	1.65	3.6	V	
VCC		Data retention only	1.5		V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}			
V_{IH}	High-level input voltage	V _{CC} = 2.3 V to 2.7 V	1.7		V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2			
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}		
V_{IL}	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8		
VI	Input voltage		0	5.5	V	
	Output voltage	High or low state	0 V _{CC}		V	
VO	Output voltage	3 state	0	5.5	V	
		V _{CC} = 1.65 V		-4		
lau	High-level output current	V _{CC} = 2.3 V		-8	mA	
IOH		V _{CC} = 2.7 V	CC = 2.7 V -1] ""	
		V _{CC} = 3 V		-24		
	Low-level output current	V _{CC} = 1.65 V		4		
lOL		V _{CC} = 2.3 V		8	mA	
		V _{CC} = 2.7 V		12		
		V _{CC} = 3 V		24		
Δt/Δν	Input transition rise or fall rate		0	10	ns/V	
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		VCC	MIN	TYP†	MAX	UNIT
	I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} -0.2				
	I _{OH} = -4 mA	1.65 V	1.2			v	
	I _{OH} = -8 mA	2.3 V	1.7				
VOH	Ιου - 12 mΔ	40. 4					V
	I _{OH} = -12 mA	3 V	2.4				
VOH VOL II Ioff IOZ ICC	I _{OH} = -24 mA	3 V	2.2				
	I _{OL} = 100 μA		1.65 V to 3.6 V			0.2	
	I _{OL} = 4 mA	1.65 V			0.45	V	
VoL	I _{OL} = 8 mA	2.3 V			0.7		
	I _{OL} = 12 mA	2.7 V			0.4		
	I _{OL} = 24 mA	3 V			0.55		
lį	V _I = 0 to 5.5 V		3.6 V			±5	μΑ
l _{off}	V _I or V _O = 5.5 V		0			±10	μΑ
loz	V _O = 0 to 5.5 V	V _O = 0 to 5.5 V				±10	μΑ
	$V_I = V_{CC}$ or GND		2.21/		,	10	
ICC	$3.6 \text{ V} \le \text{V}_{\text{I}} \le 5.5 \text{ V}^{\ddagger}$	IO = 0	3.6 V			10	μΑ
ΔlCC	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND		2.7 V to 3.6 V			500	μΑ
Ci	V _I = V _{CC} or GND		3.3 V		5		pF
Co	$V_O = V_{CC}$ or GND		3.3 V		7		pF

 $^{^{\}dagger}$ All typical values are at V_{CC} = 3.3 V, T_A = 25°C. ‡ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
	(INPOT)		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
^t pd	А	Υ	§	§	§	§		7.1	1	6.7	ns
t _{en}	ŌĒ	Y	§	§	§	§		8.5	1	7.3	ns
^t dis	ŌĒ	Y	§	§	§	§		7.3	1.8	6.7	ns
t _{sk(o)} ¶										1	ns

[§] This information was not available at the time of publication.

operating characteristics, T_A = 25°C

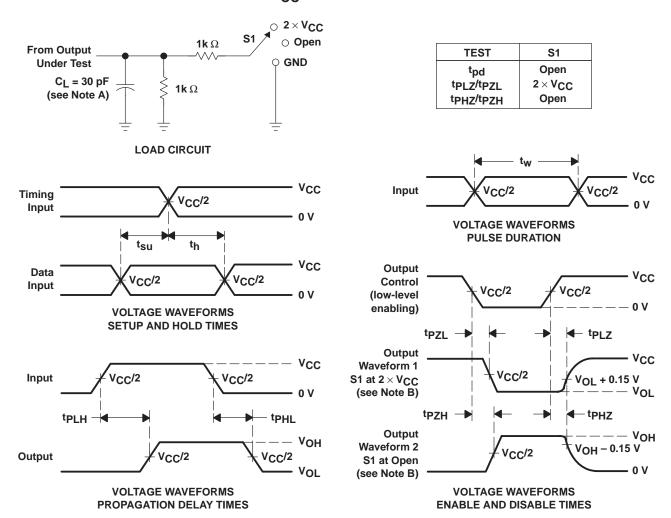
PARAMETER			TEST CONDITIONS	V _{CC} = 1.8 V ± 0.15 V	V _{CC} = 2.5 V ± 0.2 V	V _{CC} = 3.3 V ± 0.3 V	UNIT	
			CONDITIONS	TYP	TYP	TYP		
C _{pd} Power dissipation capacitance per buffer/driver		Outputs enabled	f = 10 MHz	§	§	24	pF	
		Outputs disabled	1 = 10 MH2	§	§	7	рг	

[§] This information was not available at the time of publication.



 $[\]P$ Skew between any two outputs of the same package switching in the same direction

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$

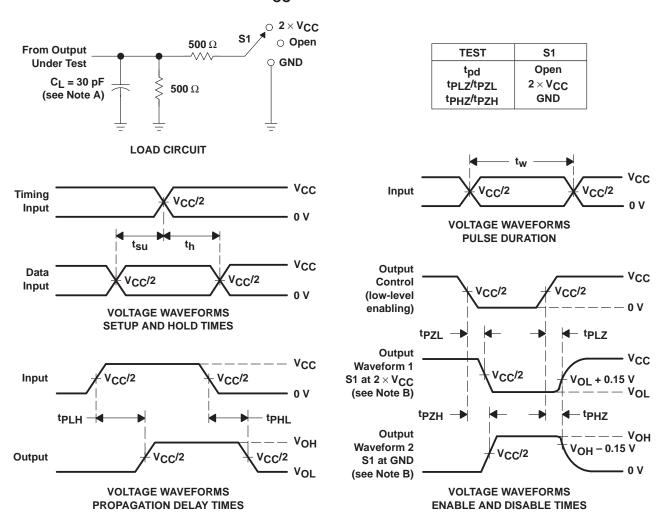


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



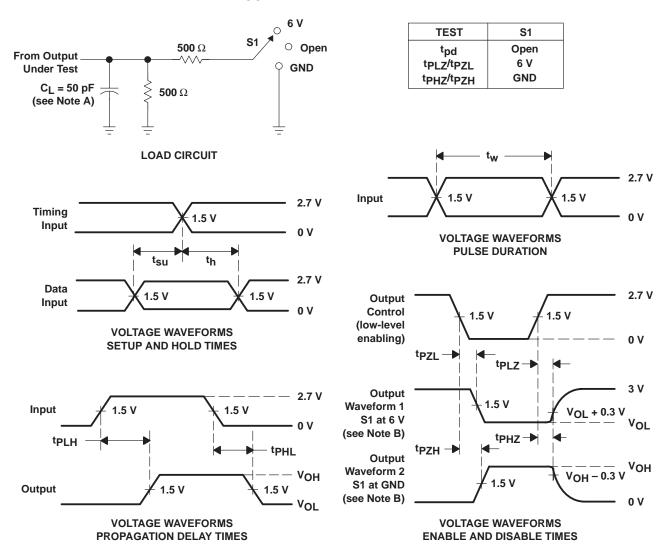
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2.5 \text{ ns.}$
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms



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